

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device is provided that includes a first conductivity type semiconductor substrate, a first conductivity type cladding layer provided on the semiconductor substrate and an active layer provided on the cladding layer. The active layer has a super-lattice structure including a disordered region in a vicinity of a cavity end face. A first cladding layer of a second conductivity type is provided on the active layer, an etching stop layer of the second conductivity type is provided on the first cladding layer and a second cladding layer of the second conductivity type is provided on the etching stop layer. The second cladding layer forms a ridge structure that extends along a cavity length direction. An impurity concentration in the etching stop layer in the vicinity of the cavity end face is equal to or smaller than about $2 \times 10^{18} \text{ cm}^{-3}$.

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